METHOD OF HARD MASK CD CONTROL BY AR SPUTTERING

ABSTRACT OF THE DISCLOSURE

A method for etching features into a silicon based etch layer through a patterned hard mask in a plasma processing chamber is provided. A silicon sputtering is provided to sputter silicon from the silicon based etch layer onto sidewalls of the patterned hard mask to form sidewalls on the patterned hard mask. The etch layer is etched through the patterned hard mask.

FIG. 1

